

Title (en)

METHOD OF PRODUCING VERY SMALL STRUCTURAL WIDTHS ON A SEMICONDUCTOR SUBSTRATE

Title (de)

VERFAHREN ZUM ERZEUGEN SEHR KLEINER STRUKTURWEITEN AUF EINEM HALBLEITERSUBSTRAT

Title (fr)

PROCEDE PERMETTANT DE CREER DES LARGEURS STRUCTURALES TRES REDUITES SUR UN SUBSTRAT A SEMI-CONDUCTEUR

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Application

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Abstract (en)

[origin: DE19534780A1] The invention concerns a method of producing a very small structural width on a semiconductor substrate (1; 10) by producing a microstructure (8; 70) as the result of isotropic etching of a first layer (6) deposited over an edge and removing the edge-forming structure (7; 60). The width of the microstructure (8; 70) is approximately the same thickness as the deposited first layer. An underlying polysilicon (5, 50) layer is then selectively oxidised. The small structural width can be the cross section through the channel of a flasch memory cell.

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